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Date Submitted: October 9, 2003

(use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	~~Unassigned~~ 10/681,318
Filing Date	October 9, 2003
First Named Inventor	Hisayo MOMOSE
Group Art Unit	2826
Examiner Name	~~Unassigned~~ Minh-Loan Tran
Attorney Docket Number	016887-1094

C/Class
Sub Class

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	U.S. Patent Document Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
MLT	A1	5,508,543		HARTSTEIN et al.	04-16-1996	
	A2	5,463,234		TORIUMI et al.	10-31-1995	
	A3	5,436,481		EGAWA et al.	07-25-1995	
	A4	5,412,527		HUSHER	05-02-1995	
	A5	4,814,851		ABROKWAH et al.	03-21-1989	
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document Office[3]	Number[4]	Kind Code[5] (if known)	Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
MLT	A8	JP	5/275690			10-1993		
MLT	A9	EP	196 155			10-1986		
MLT	A10	GB	2172746			09-1986		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
MLT	A11	MOMOSE et al., "Tunneling Gate Oxide Approach to Ultra-High Current Drive in Small-Geometry MOSFETS", 1994 International Electron Devices Meeting, pp. 593-596.	
MLT	A12	FIEGNA et al., "A New Scaling Methodology for the 0.1-0.025 μm MOSFET, 1993 Symposium on VLSI Technology, pp. 33-34.	
MLT	A13	ONO et al., "Sub-50 nm Gate Length N-MOSFETS with 10 nm Phosphorus Source and Drain Junctions, 1993 International Electron Devices Meeting, pp. 119-122.	

Examiner Signature	Minhloan Tran	Date Considered	11/04

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